(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
20 November 2008 (20.11.2008)

PCT

(10) International Publication Number
WO 2008/140876 A1

(51) International Patent Classification:
H01L 21/8242 (2006.01) *H01L 27/12* (2006.01)
H01L 21/84 (2006.01) *H01L 29/78* (2006.01)
H01L 27/108 (2006.01) *H01L 21/762* (2006.01)

(21) International Application Number:
PCT/US2008/059788

(22) International Filing Date: 9 April 2008 (09.04.2008)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
11/745,783 8 May 2007 (08.05.2007) US

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, NO, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *with international search report*
— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*

(54) **Title:** MEMORY ARRAYS, SEMICONDUCTOR CONSTRUCTIONS AND ELECTRONIC SYSTEMS; AND METHODS OF FORMING MEMORY ARRAYS, SEMICONDUCTOR CONSTRUCTIONS AND ELECTRONIC SYSTEMS

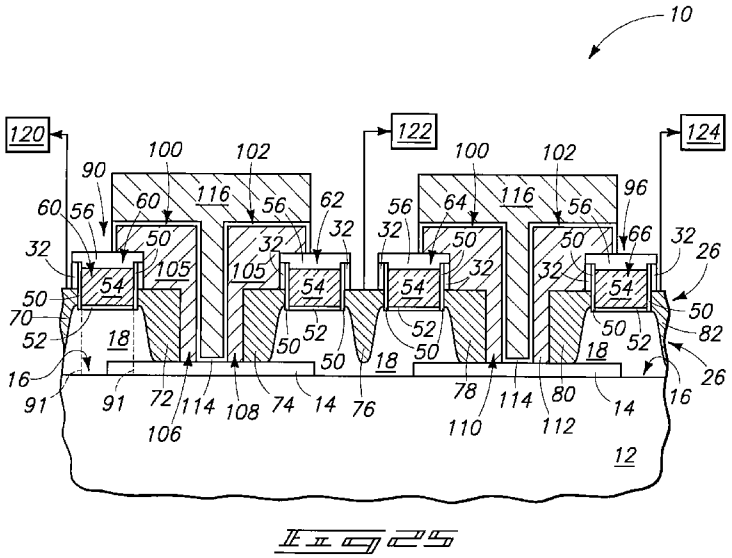


Fig 25

(57) **Abstract:** The present invention, relates to semiconductor constructions over partial SOI substrate, and manufacturing methods therefor. Some embodiments include DRAM (10) having transistor gates (54) extending partially over SOI (19), and methods of forming such DRAM. Unit cells of the DRAM may be within active region pedestals (18), and in some embodiments the unit cells may comprise capacitors having storage nodes (106, 108, 110, 112) in direct contact with sidewalls of the active region pedestals. Some embodiments include OC1 T memory having transistor gates entirely over SOI, and methods of forming such OC1 T memory.

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